

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	100	(VCSEL OR VLSEA) and (semiconductor near3 (layer or film or medium or region or type or material) near3 dop\$4) and (mirror\$1 or reflect\$4) and ((lattice near3 mismatch\$3) or (trap\$4 near4 defect\$3)) and (active or gain) and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 13:37
L2	37	(VCSEL OR VLSEA) and (semiconductor near3 (layer or film or medium or region or type or material) near3 dop\$4) and (mirror\$1 or reflect\$4) and ((lattice near3 mismatch\$3) or (trap\$4 near4 defect\$3)) and (active or gain) and substrate and "372"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 13:37
L4	1	((VCSEL OR VLSEA) and (semiconductor near3 (layer or film or medium or region or type or material) near3 dop\$4) and (mirror\$1 or reflect\$4) and ((lattice near3 mismatch\$3) or (trap\$4 near4 defect\$3)) and (active or gain) and substrate). CLM.	US-PGPUB	AND	ON	2005/12/07 13:38
L6	1	laser and ((dop\$4 near3 (layer or type or medium or film)) laser (semiconductor near3 (layer or film or medium or region or type or material))) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3) and (bulk near3 dop\$4) and "372"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 13:39
L5	2	laser and ((dop\$4 near3 (layer or type or medium or film)) laser (semiconductor near3 (layer or film or medium or region or type or material))) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3) and (bulk near3 dop\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 13:41
L8	1	laser and ((dop\$4 near3 (layer or type or medium or film)) laser (semiconductor near3 (layer or film or medium or region or type or material))) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3) and (bulk near3 dop\$4) and (active or gain) and pump and VCSEL	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 13:42
L11	255	((Verma near3 Ashish) or (Chen near3 Arnold) or (Francis near3 Daniel)).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 13:44
L3	1	((VCSEL OR VLSEA) and (semiconductor near3 (layer or film or medium or region or type or material) near3 dop\$4) and (mirror\$1 or reflect\$4) and ((lattice near3 mismatch\$3) or (trap\$4 near4 defect\$3)) and (active or gain) and substrate). CLM.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 13:45
L9	1	laser and ((dop\$4 near3 (layer or type or medium or film)) with (semiconductor near3 (layer or film or medium or region or type or material))) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3) and (bulk near3 dop\$4) and (active or gain) and pump and VCSEL	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 13:45
L12	1	laser and ((dop\$4 near3 (layer or type or medium or film)) with (semiconductor near3 (layer or film or medium or region or type or material))) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3) and (bulk near3 dop\$4) and (active or gain) and pump and VCSEL and 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 13:45
L13	0	(laser and ((dop\$4 near3 (layer or type or medium or film)) laser (semiconductor near3 (layer or film or medium or region or type or material))) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3) and (bulk near3 dop\$4)).CLM.	US-PGPUB	AND	ON	2005/12/07 13:45

L7	1	(laser and ((dop\$4 near3 (layer or type or medium or film)) laser (semiconductor near3 (layer or film or medium or region or type or material))) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3) and (bulk near3 dop\$4)).CLM.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 13:46
L10	0	(laser and ((dop\$4 near3 (layer or type or medium or film)) with (semiconductor near3 (layer or film or medium or region or type or material))) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3) and (bulk near3 dop\$4) and (active or gain) and pump and VCSEL).CLM.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 13:46
L14	1	((VCSEL OR VLSEA) and (semiconductor near3 (layer or film or medium or region or type or material) near3 dop\$4) and (mirror\$1 or reflect\$4) and ((lattice near3 mismatch\$3) or (trap\$4 near4 defect\$3)) and (active or gain) and substrate).CLM.	US-PGPUB	AND	ON	2005/12/07 13:46
L15	0	(laser and ((dop\$4 near3 (layer or type or medium or film)) laser (semiconductor near3 (layer or film or medium or region or type or material))) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3) and (bulk near3 dop\$4)).CLM.	US-PGPUB	AND	ON	2005/12/07 13:46
L16	0	(laser and ((dop\$4 near3 (layer or type or medium or film)) with (semiconductor near3 (layer or film or medium or region or type or material))) and (mirror or reflect\$4) and (trap\$4 near2 defect\$4) and (lattice near3 mismatch\$3) and (bulk near3 dop\$4) and (active or gain) and pump and VCSEL).CLM.	US-PGPUB	AND	ON	2005/12/07 13:46